

# FDPF18N20FT\_G

## N-Channel UniFET™ FRFET® MOSFET

### 200 V, 18 A, 140 m

#### Features

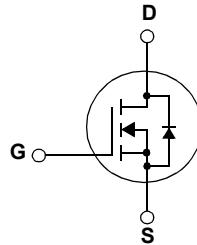
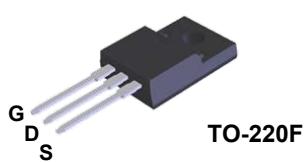
- $R_{DS(on)} = 129 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 9 \text{ A}$
- Low Gate Charge (Typ. 20 nC)
- Low  $C_{rss}$  (Typ. 24 pF)
- 100% Avalanche Tested
- Improve dv/dt Capability
- RoHS Compliant

#### Applications

- LCD/LED TV
- Consumer Appliances
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

#### Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. The body diode's reverse recovery performance of UniFET FRFET® has been enhanced by lifetime control. Its  $t_{rr}$  is less than 100nsec and the reverse dv/dt immunity is 15V/ns while normal planar MOSFETs have over 200nsec and 4.5V/ns respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



#### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter		FDPF18N20FT_G	Unit
$V_{DSS}$	Drain to Source Voltage		200	V
$V_{GSS}$	Gate to Source Voltage		$\pm 30$	V
$I_D$	Drain Current	-Continuous ( $T_C = 25^\circ\text{C}$ )	18*	A
		-Continuous ( $T_C = 100^\circ\text{C}$ )	10.8*	
$I_{DM}$	Drain Current	- Pulsed	(Note 1)	A
$E_{AS}$	Single Pulsed Avalanche Energy		(Note 2)	mJ
$I_{AR}$	Avalanche Current		(Note 1)	A
$E_{AR}$	Repetitive Avalanche Energy		(Note 1)	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$		(Note 3)	V/ns
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	35	W
		- Derate above $25^\circ\text{C}$	0.27	
$T_J, T_{STG}$	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	$^\circ\text{C}$

\*Drain current limited by maximum junction temperature

#### Thermal Characteristics

Symbol	Parameter	FDPF18N20FT_G	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.6	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case to Sink, Typ.	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

## Package Marking and Ordering Information $T_C = 25^\circ\text{C}$ unless otherwise noted

Device Marking	Device	Package	Eco Status	Reel Size	Tape Width	Quantity
FDPF18N20FT	FDPF18N20F_G	TO-220F	Green/RoHS	-	-	50



For Fairchild's definition of "green" Eco Status, please visit: [http://www.fairchildsemi.com/company/green/rohs\\_green.html](http://www.fairchildsemi.com/company/green/rohs_green.html)

## Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
--------	-----------	-----------------	------	------	------	------

### Off Characteristics

$\text{BV}_{\text{DSS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$	200	-	-	V
$\frac{\Delta \text{BV}_{\text{DSS}}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.2	-	$^\circ\text{C}$
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{V}, V_{GS} = 0\text{V}$	-	-	10	$\mu\text{A}$
		$V_{DS} = 160\text{V}, T_C = 125^\circ\text{C}$	-	-	100	
$I_{\text{GSS}}$	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	3.0	-	5.0	V
$R_{DS(\text{on})}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 9\text{A}$	-	0.12	0.14	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20\text{V}, I_D = 9\text{A}$ (Note 4)	-	13.6	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	885	1180	pF
$C_{oss}$	Output Capacitance		-	200	270	pF
$C_{rss}$	Reverse Transfer Capacitance		-	24	35	pF
$Q_{g(\text{tot})}$	Total Gate Charge at $10\text{V}$		-	20	26	nC
$Q_{gs}$	Gate to Source Gate Charge	$V_{DS} = 160\text{V}, I_D = 18\text{A}$ $V_{GS} = 10\text{V}$	-	5	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge	(Note 4, 5)	-	9	-	nC

### Switching Characteristics

$t_{d(\text{on})}$	Turn-On Delay Time	$V_{DD} = 100\text{V}, I_D = 18\text{A}$ $R_G = 25\Omega$	-	16	40	ns
$t_r$	Turn-On Rise Time		-	50	110	ns
$t_{d(\text{off})}$	Turn-Off Delay Time		-	50	110	ns
$t_f$	Turn-Off Fall Time		(Note 4, 5)	-	40	90

### Drain-Source Diode Characteristics

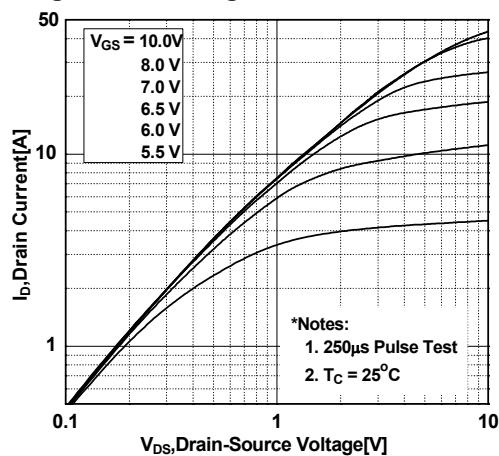
$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	-	18	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	72	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}, I_{SD} = 18\text{A}$	-	-	1.5	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{V}, I_{SD} = 18\text{A}$	-	80	-	ns
$Q_{rr}$	Reverse Recovery Charge	$dl_f/dt = 100\text{A}/\mu\text{s}$	(Note 4)	-	240	nC

#### Notes:

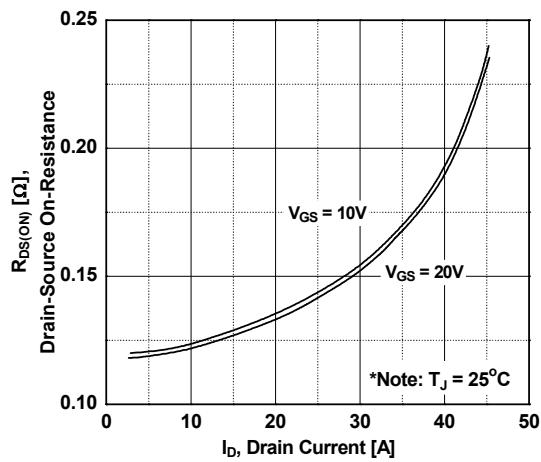
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L = 2\text{mH}, I_{AS} = 18\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 18\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq \text{BV}_{\text{DSS}}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

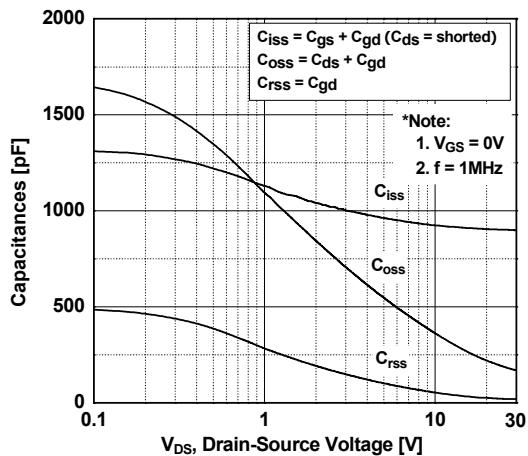
**Figure 1. On-Region Characteristics**



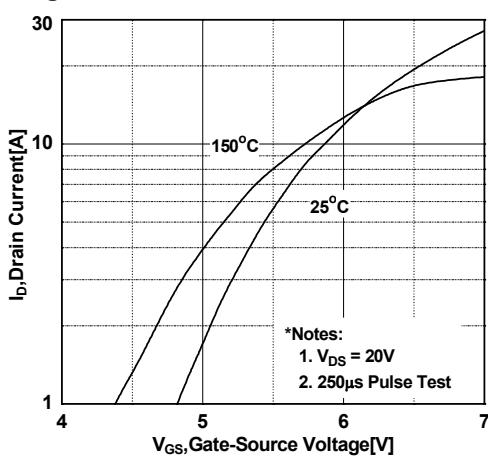
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



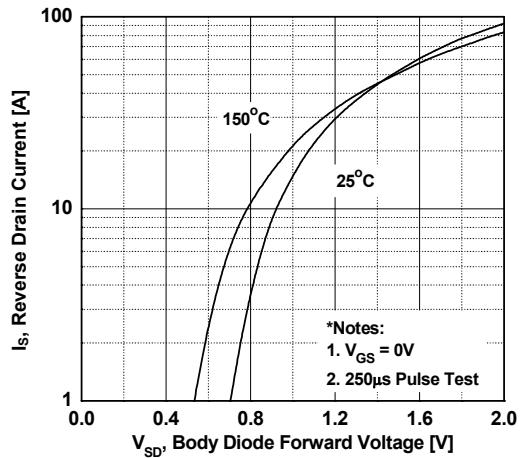
**Figure 5. Capacitance Characteristics**



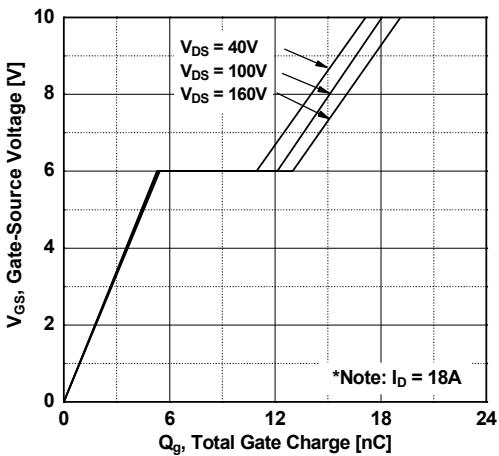
**Figure 2. Transfer Characteristics**



**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**

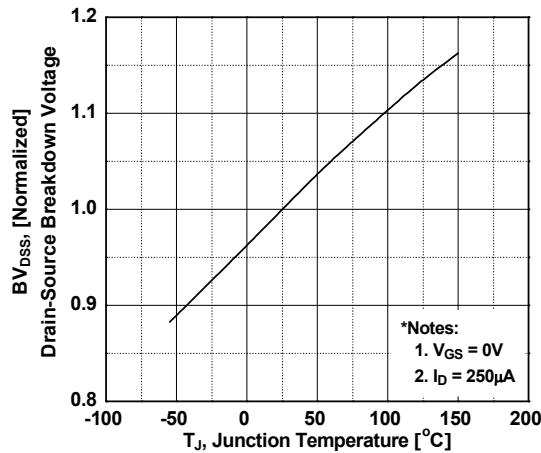


**Figure 6. Gate Charge Characteristics**

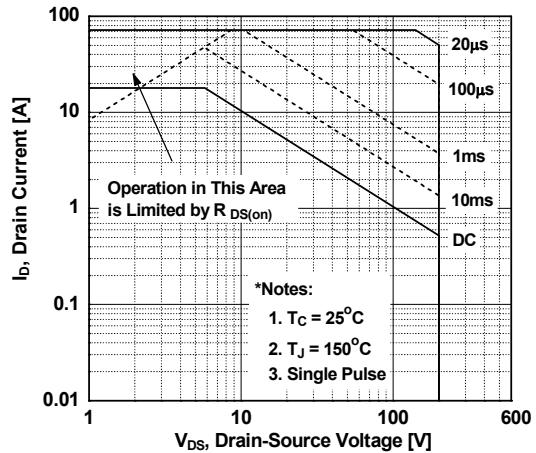


**Typical Performance Characteristics (Continued)**

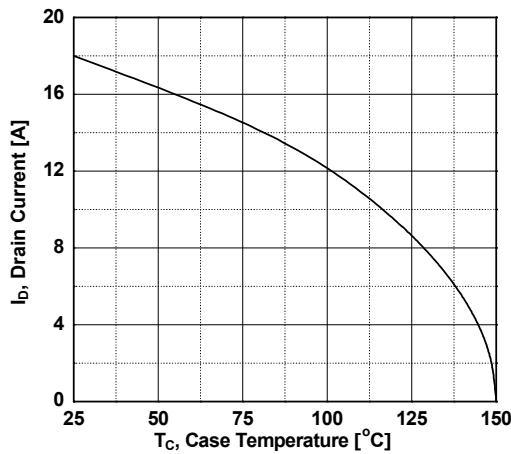
**Figure 7. Breakdown Voltage Variation vs. Temperature**



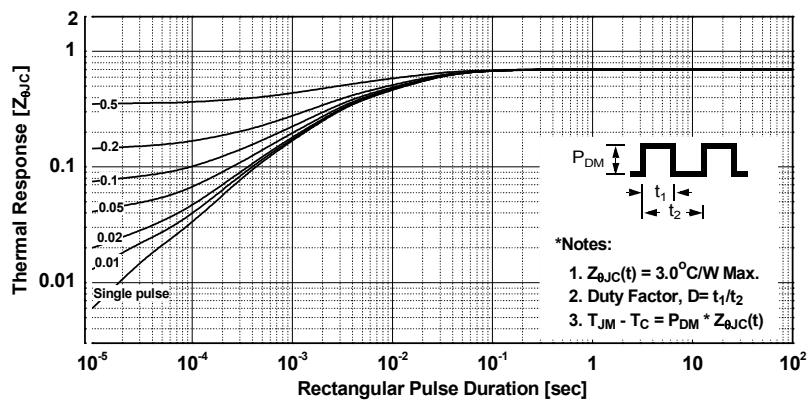
**Figure 8. Maximum Safe Operating Area - FDP18N20F**



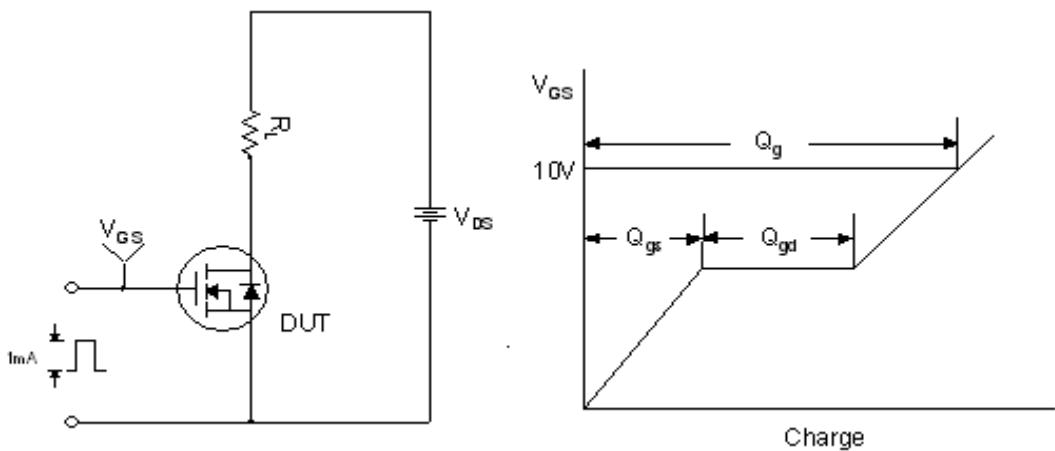
**Figure 9. Maximum Drain Current vs. Case Temperature**



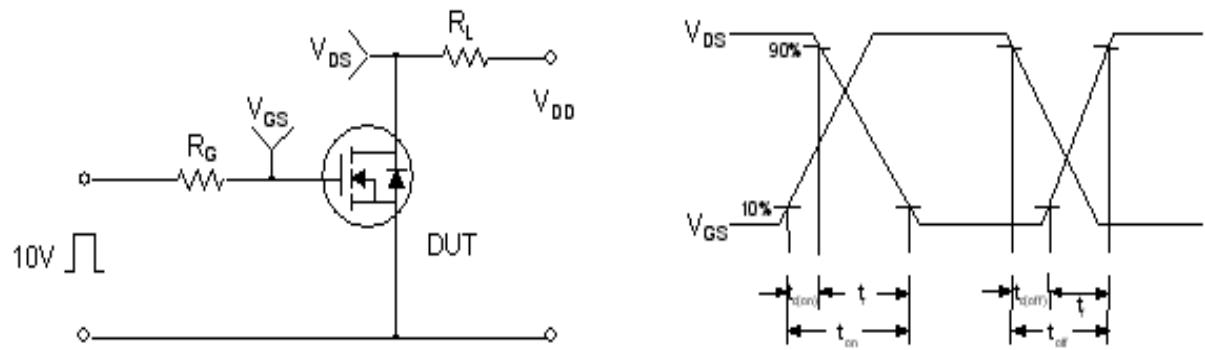
**Figure 10. Transient Thermal Response Curve - FDP18N20F**



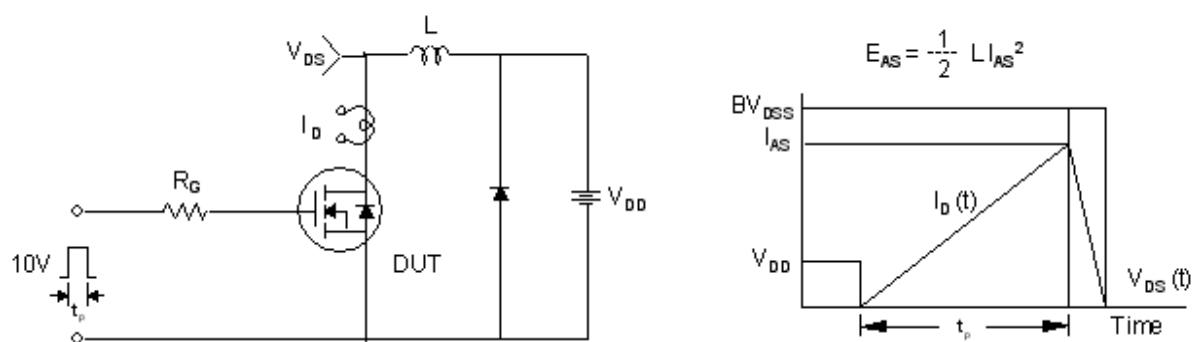
Gate Charge Test Circuit & Waveform



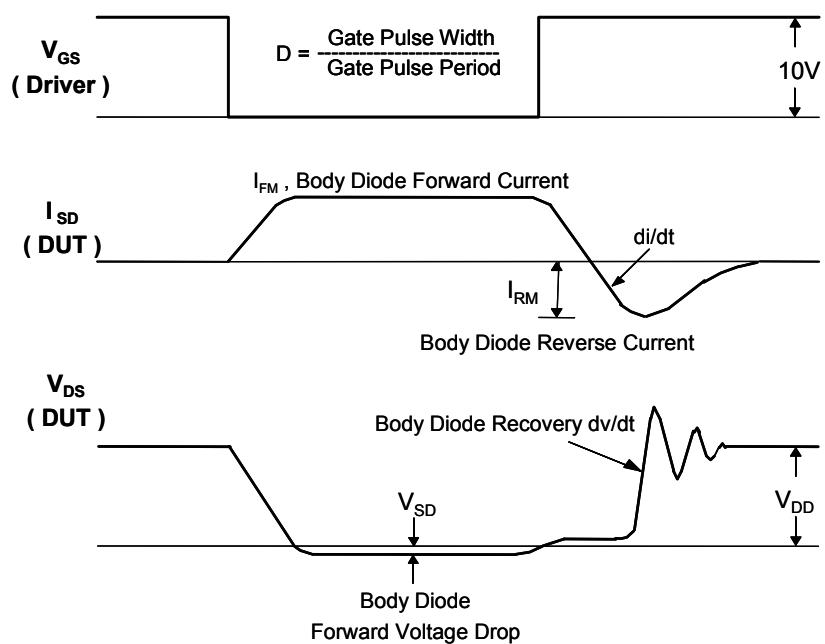
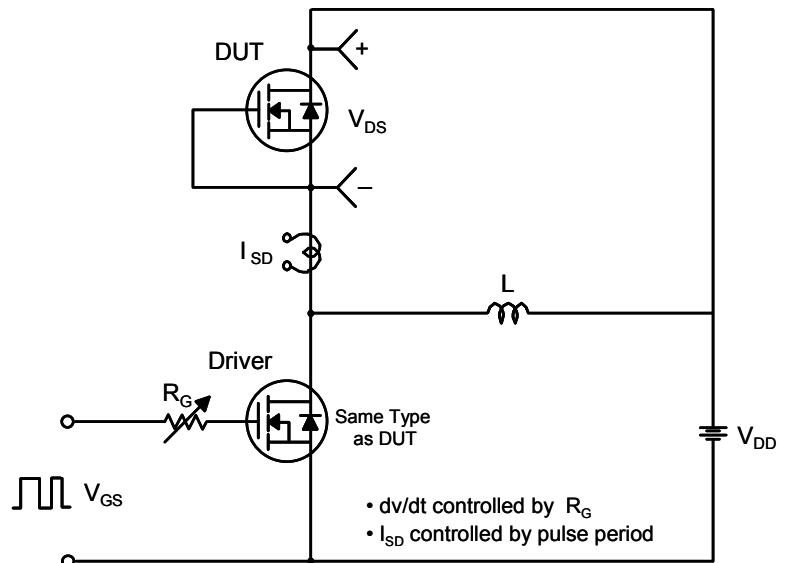
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

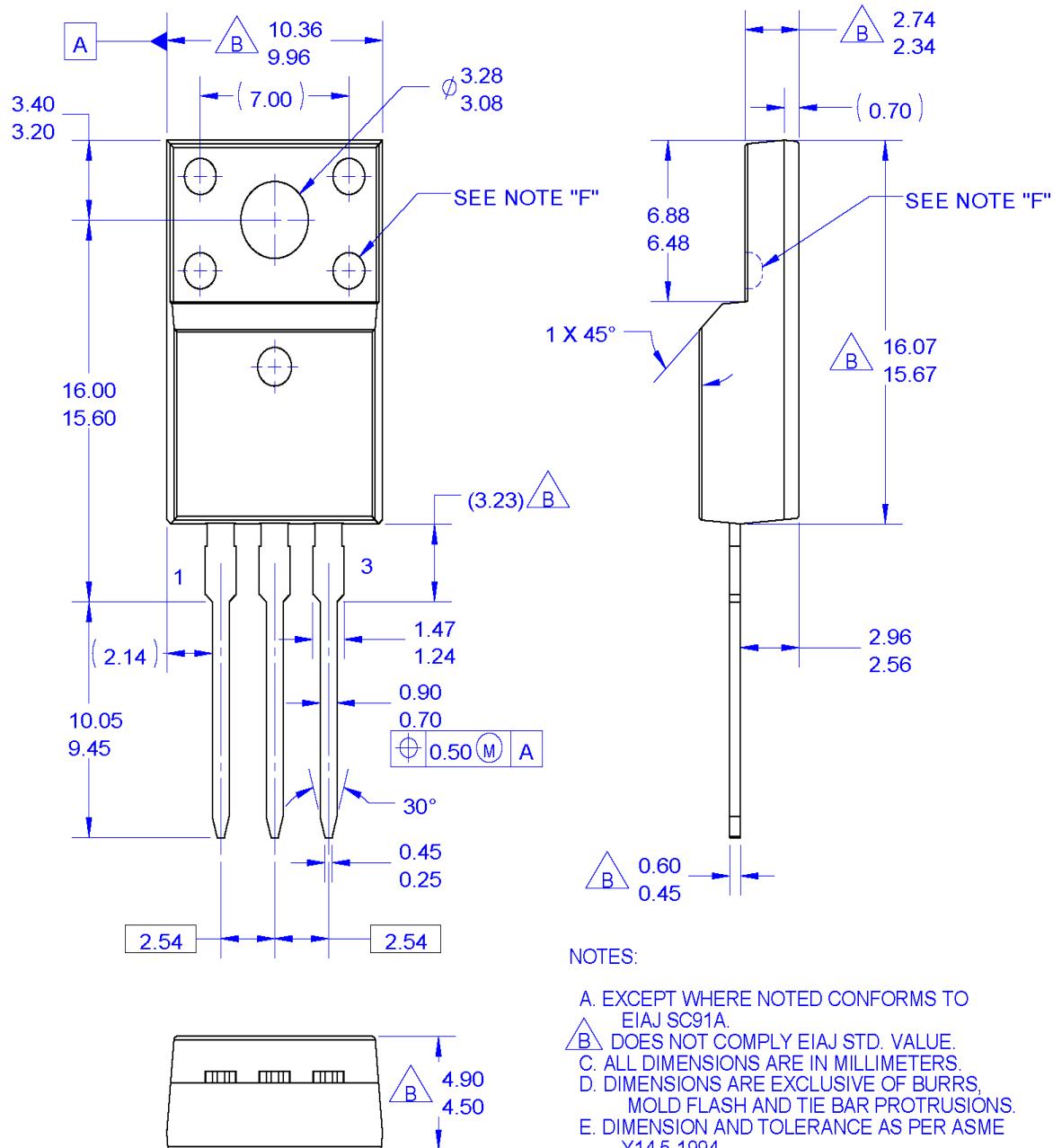


Peak Diode Recovery dv/dt Test Circuit & Waveforms



## Mechanical Dimensions

TO-220M03



Dimensions in Millimeters


**TRADEMARKS**

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

2Cool™  
AccuPower™  
AX-CAP®\*  
BitSiC™  
Build it Now™  
CorePLUS™  
CorePOWER™  
CROSSVOLT™  
CTL™  
Current Transfer Logic™  
DEUXPEED®  
Dual Cool™  
EcoSPARK®  
EfficientMax™  
ESBC™  
  
Fairchild®  
Fairchild Semiconductor®  
FACT Quiet Series™  
FACT®  
FAST®  
FastvCore™  
FETBench™

FPS™  
F-PFS™  
FRFET®  
Global Power Resource™  
Green Bridge™  
Green FPS™  
Green FPS™ e-Series™  
Gmax™  
GTO™  
IntelliMAX™  
ISOPLANAR™  
Marking Small Speakers Sound Louder and Better™  
MegaBuck™  
MICROCOUPLER™  
MicroFET™  
MicroPak™  
MicroPak2™  
MillerDrive™  
MotionMax™  
mWSaver™  
OptoHiT™  
OPTOLOGIC®  
OPTOPLANAR®

PowerTrench®  
PowerXS™  
Programmable Active Droop™  
QFET®  
QST™  
Quiet Series™  
RapidConfigure™  
  
Saving our world, 1mW/W/kW at a time™  
SignalWise™  
SmartMax™  
SMART START™  
Solutions for Your Success™  
SPM®  
STEALTH™  
SuperFET®  
SuperSOTT™-3  
SuperSOTT™-6  
SuperSOTT™-8  
SupreMOS®  
SyncFET™

Sync-Lock™  
  
TinyBoost™  
TinyBuck™  
TinyCalc™  
TinyLogic®  
TINYOPTO™  
TinyPower™  
TinyPWM™  
TinyWire™  
TransiC®  
TriFault Detect™  
TRUECURRENT®\*  
μSerDes™  
  
UHC®  
Ultra FRFET™  
UniFET™  
VCX™  
VisualMax™  
VoltagePlus™  
XS™

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

**DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

**LIFE SUPPORT POLICY**

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

**ANTI-COUNTERFEITING POLICY**

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, [www.Fairchildsemi.com](http://www.Fairchildsemi.com), under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

**PRODUCT STATUS DEFINITIONS**
**Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I64